1. General description

NPN high power bipolar transistor in a power SOT1289B (CFP15B) flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- · High thermal power dissipation capability
- High energy efficiency due to less heat generation
- High current gain at V_{CE} = 60 V
- · Electrically similar to popular MJD31 series
- · Low collector emitter saturation voltage
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Power management
- · Load switch
- Linear mode voltage regulator
- Constant current drive backlighting application
- Motor drive
- · Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	5	Α
h _{FE}	DC current gain	V_{CE} = 60 V; I_{C} = 20 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	120	-	-	
		V_{CE} = 4 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	-	-	
		V_{CE} = 4 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	25	-	-	
		V_{CE} = 4 V; I_{C} = 3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	10	-	-	



100 V, 3 A NPN high power bipolar transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	<u></u>	С
2	В	base		
3	С	collector	3 3	B — (
			CFP15B (SOT1289B)	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
MJPE31CH-Q		plastic, thermal enhanced ultra thin SMD package; 3 leads; 2.13 mm pitch; 5.8 x 4.3 x 0.95 mm body	SOT1289B				

7. Marking

Table 4. Marking codes

Type number	Marking code
MJPE31CH-Q	MJPE31CH

100 V, 3 A NPN high power bipolar transistor

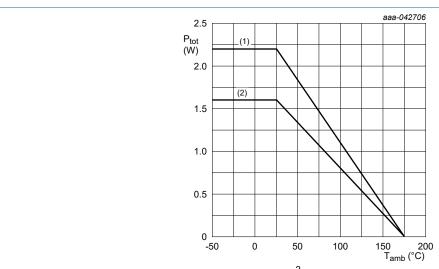
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	100	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.6	W
		T _{amb} ≤ 25 °C	[2]	-	2.2	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), 140 µm single-sided copper, standard footprint.
- 2] Device mounted on an FR4 Printed-Circuit Board (PCB), 140 μm single-sided copper, mounting pad for collector 1 cm².



- (1) FR4 PCB, single-sided 140 µm copper, 1 cm²
- (2) FR4 PCB, single-sided 140 µm copper, standard footprint

Fig. 1. Power derating curves

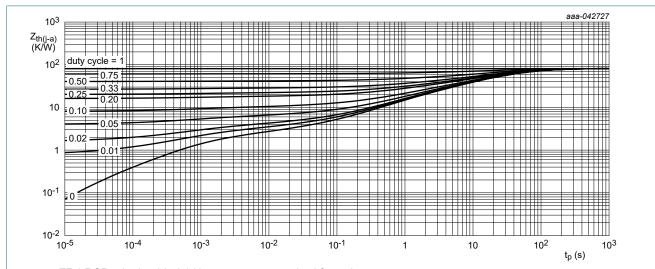
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9. Thermal characteristics

Table 6. Thermal characteristics

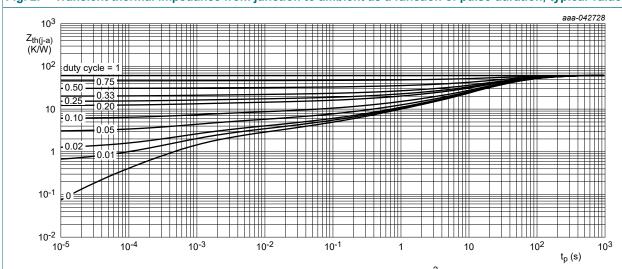
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	94	K/W
	junction to ambient		[2]	-	-	69	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	4.5	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), 140 µm single-sided copper, standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), 140 μm single-sided copper, mounting pad for collector 1cm².



FR4 PCB, single-sided 140 µm copper, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided 140 µm copper, mounting pad for collector 1 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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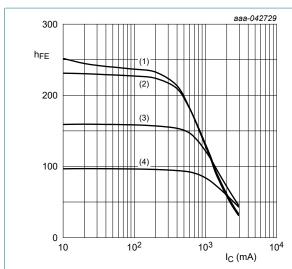
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	I	Min	Тур	Max	Unit
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$,	100	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_C = 0 \text{ A}; I_E = 100 \mu\text{A}; T_{amb} = 25 \text{ °C}$	6	5	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	•	-	1	μA
I _{CES}		V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	•	-	1	μΑ
	current	V _{CE} = 80 V; V _{BE} = 0 V; T _j = 150 °C	-	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	•	-	1	μΑ
h _{FE}	DC current gain	V_{CE} = 60 V; I_{C} = 20 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	,	120	-	-	
		V_{CE} = 4 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	,	100	-	-	
		V_{CE} = 4 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	2	25	-	-	
		V_{CE} = 4 V; I_{C} = 3 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	,	10	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 3 A; I_B = 375 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	•	-	1.2	V
V_{BE}	base-emitter voltage	V_{CE} = 4 V; I_{C} = 3 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	•	-	1.8	V
h _{fe}	small-signal current gain	V_{CE} = 10 V; I_{C} = 500 mA; f = 1 kHz; T_{amb} = 25 °C	2	20	-	-	
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 500 mA; f = 100 MHz; T_{amb} = 25 °C	3	3	130	-	MHz

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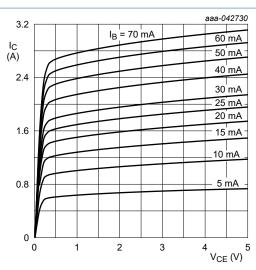


 $V_{CE} = 4 V$

 $(1) T_{amb} = 175 °C$

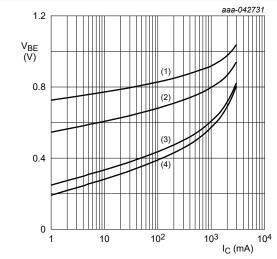
(2) T_{amb} = 150 °C (3) T_{amb} = 25 °C (4) T_{amb} = -55 °C

Fig. 4. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $V_{CE} = 4 V$

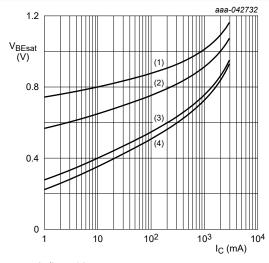
(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

(4) $T_{amb} = 175 \, ^{\circ}C$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



 $I_{C}/I_{B} = 10$ (1) $T_{amb} = -55 \,^{\circ}C$

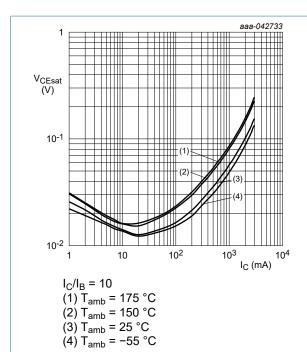
(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

(3) $T_{amb} = 175 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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(4) I_{amb} = −55 °C Fig. 8. Collector-emitter saturation voltage as a

function of collector current; typical values

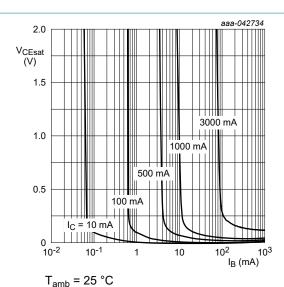


Fig. 9. Collector-emitter saturation region as a function

of base current; typical values

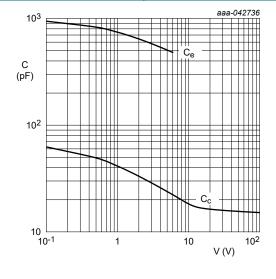


Fig. 10. Input/output capacitance as a function of input/output voltage

11. Test information

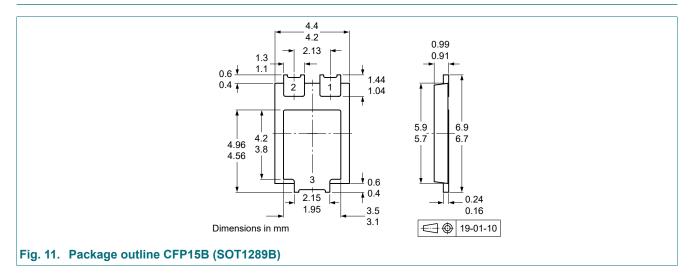
T_{amb} = 25 °C

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

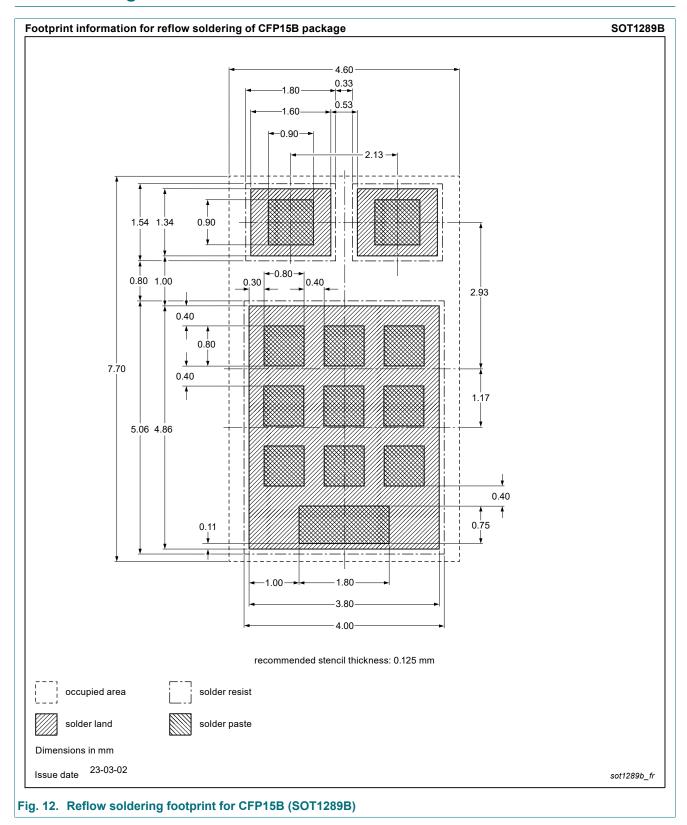
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

- and the state of							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
MJPE31CH-Q v.2	20250422	Product data sheet	-	MJPE31CH-Q v.1			
Modifications:	Product status chang	Product status changed					
MJPE31CH-Q v.1	20250402	Preliminary data sheet	-	-			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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